Analog Power AM20N15-250B MOSFET Datasheet

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Key Features:
Low rDS(on) trench technology
Low thermal impedance
Fast switching speed
Typical Applications:
White LED boost converters
Automotive Systems
Industrial DC/DC Conversion Circuits

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N-Channel 150-V (D-S) MOSFET

Key Features:

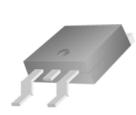
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

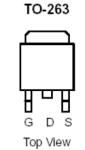
Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY					
V _{DS} (V)	$r_{DS(on)}(m\Omega)$				
150	200 @ V _{GS} = 10V	21 ^a			
130	225 @ V _{GS} = 5.5V	21			







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter			Limit	Units			
Drain-Source Voltage	V_{DS}	150	V				
Gate-Source Voltage	V_{GS}	±20	V				
Continuous Drain Current a	T _C =25°C	I_D	21 A				
Pulsed Drain Current ^b		I _{DM}	80	ζ			
Continuous Source Current (Diode Conduction) ^a		I _S	110	Α			
Power Dissipation ^a	T _C =25°C	P_{D}	300	W			
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	62.5	°C/W			
Maximum Junction-to-Case	$R_{\theta JC}$	1	C/VV			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

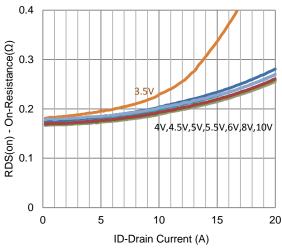
Parameter	Symbol	Symbol Test Conditions		Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$			1	uА	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 16.8 \text{ A}$			200	mΩ	
Dialii-Source Oil-Resistance	r _{DS(on)}	$V_{GS} = 5.5 \text{ V}, I_D = 13.4 \text{ A}$			225	11177	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		24		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 30 \text{ A}, V_{GS} = 0 \text{ V}$		0.99		V	
		Dynamic					
Total Gate Charge	Q_g	$V_{DS} = 50 \text{ V}, V_{GS} = 5.5 \text{ V},$		11		nC	
Gate-Source Charge	Q_{gs}	$I_{DS} = 30 \text{ V}, V_{GS} = 3.3 \text{ V},$ $I_{D} = 16.8 \text{ A}$		3.6			
Gate-Drain Charge	Q_gd	1g = 10.0 A		4.3			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 75 \text{ V}, R_1 = 4.4 \Omega,$		16		ns	
Rise Time	t _r	$V_{DS} = 73 \text{ V}, K_L - 4.4 \Omega,$ $I_D = 16.8 \text{ A},$		24			
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		32			
Fall Time	t _f	v _{GEN} = 10 v, r(_{GEN} = 0.22		20			
Input Capacitance	C _{iss}			1233			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		59		pF	
Reverse Transfer Capacitance	C_{rss}			38			

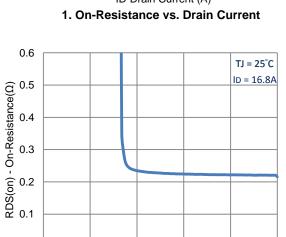
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics





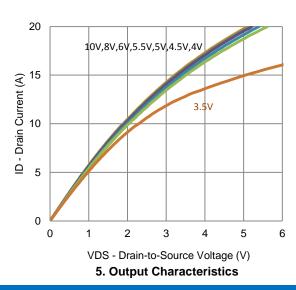
VGS - Gate-to-Source Voltage (V)
3. On-Resistance vs. Gate-to-Source Voltage

6

10

0

2

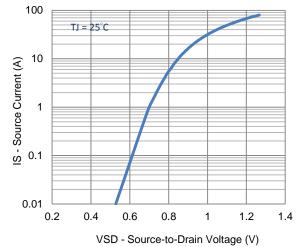


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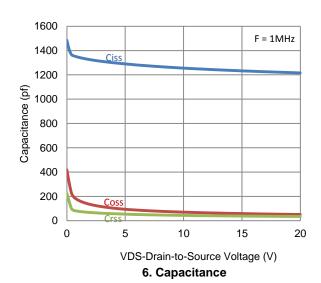
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2. Transfer Characteristics



4. Drain-to-Source Forward Voltage

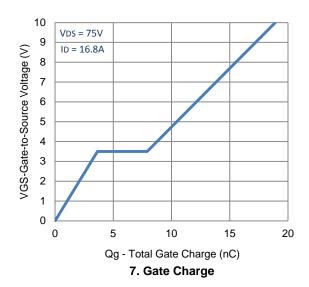


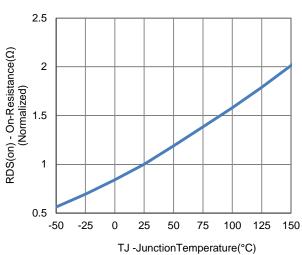
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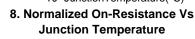
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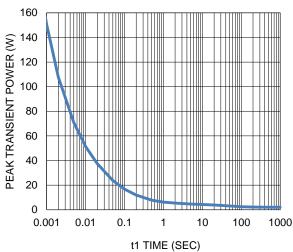
Typical Electrical Characteristics





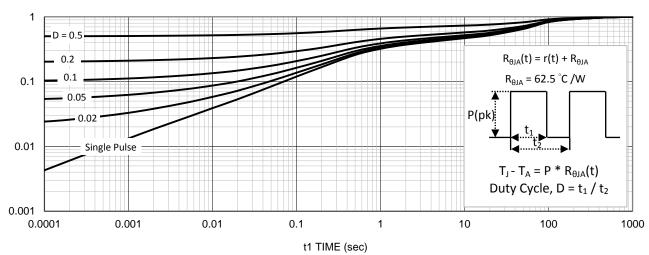
1000
100 us
100 us
100 us
1 ms
100 ms
100 ms
100 ms
100 ms
100 sec
100





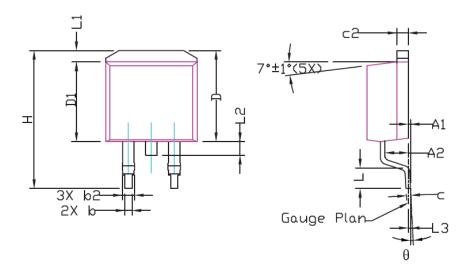
9. Safe Operating Area 1

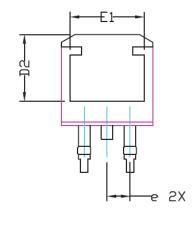




11. Normalized Thermal Transient Junction to Ambient

Package Information





CVADEI	DIMENS:	ONAL F	REQMTS	INCH	ES REG	2TM	
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX	
Α	4,30	4.57	4.72	0.169	0.180	0.186	
A1	0	-	0,25	0		0.010	
A2	2,47	2.57	2,67	0.097	0.101	0.105	
b	0.69	0,813	0.94	0.027	0.032	0.037	
b2	1.17	1.27	1,45	0.046	0.050	0.057	
С	0.48	0,50	0,60	0.019	0.020	0.024	
c2	1.17	1.27	1.37	0,046	0,050	0,054	
D	9,80	10.05	10,30	0.386	0,396	0.406	
D1	8,64	8.78	9,65	0,340	0,346	0,380	
D2	7,12	7.37	7,62	0.280	0,290	0,300	
E	9,70	10.15	10.54	0,382	0,400	0.415	
E1	8,00	8,20	8,40	0.315	0,323	0.331	
е	2	54 BSC		0.	0.100 BSC		
H	14.99	15.24	15,49	0.590	0.600	0.610	
L	1,78	2,29	2.79	0.070	0.090	0.110	
L1	1,02	1.27	1.52	0.040	0.050	0,060	
L2			1.75			0.069	
L3		0,254			0.010		
θ	0.		8*	0.		8°	